

## Errata

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### Radiation and Spontaneous Annealing of Radiation-sensitive Field-effect Transistors with Gate Oxide Thicknesses of 400 and 1000 nm

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On page 2111, in the last column of Table 1:

Table 1  
RADFET characteristics, experimental conditions and sensitivity  $S$ .

$t_{ox}$ (nm)	Label of used RADFET	$V_{G,i}$ (V)	$V_{G,a}$ (V)	$V_{T0}$ (V)	$S$ (V/Gy)
400	TYNDALL 04 P-3460 W4 3607 015	0	0	3.46	0.17778
	TYNDALL 04 P-3460 W4 3607 018	5	0	3.49	0.0287
1000	TYNDALL 04 X1370 W4 3109 045	0	0	1.96	0.288
	TYNDALL 04 X1370 W4 3109 046	5	0	2.16	0.04592

should be (the sensitivity values are mixed):

Table 1  
RADFET characteristics, experimental conditions and sensitivity  $S$ .

$t_{ox}$ (nm)	Label of used RADFET	$V_{G,i}$ (V)	$V_{G,a}$ (V)	$V_{T0}$ (V)	$S$ (V/Gy)
400	TYNDALL 04 P-3460 W4 3607 015	0	0	3.46	0.0287
	TYNDALL 04 P-3460 W4 3607 018	5	0	3.49	0.0459
1000	TYNDALL 04 X1370 W4 3109 045	0	0	1.96	0.1778
	TYNDALL 04 X1370 W4 3109 046	5	0	2.16	0.2880